Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A method of fabricating a light emitting device, comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

forming an electrode made of the second conductive film by etching the second conductive film;

adding an n-type impurity element to the semiconductor film by self-alignment using the electrode made of the second conductive film as a mask;

forming an electrode made of the first conductive film by etching the first conductive film by self-alignment using the electrode made of the second conductive film as a mask after forming the electrode made of the second conductive film;

forming a second gate electrode by narrowing a line width of the electrode made of the second conductive film by etching;

adding an n-type impurity element to the semiconductor film by self-alignment using the second gate electrode as a mask; and

forming a first gate electrode by narrowing a line width of the electrode made of the first conductive film by etching.

2. (Currently amended) A method of fabricating a light emitting device, comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

forming an electrode made of the second conductive film by etching the second conductive film;

adding an n-type impurity element to the semiconductor film by using the electrode made of the second conductive film as a mask and by making the n-type impurity element pass through the first conductive film;

forming an electrode made of the first conductive film by etching the first conductive film by self-alignment using the electrode made of the second conductive film as a mask;

forming a second gate electrode by narrowing a line width of the electrode made of the second conductive film by etching;

adding an n-type impurity element to the semiconductor film by using the second gate electrode as a mask and by making the n-type impurity element pass through the electrode made of the first conductive film; and

forming a first gate electrode by narrowing a line width of the electrode made of the first conductive film by etching.

3. (Currently amended) A method of fabricating an electrical appliance having a light emitting device, comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

forming an electrode made of the second conductive film by etching the second conductive film;

adding an ~~n-type~~ impurity element to the semiconductor film by self-alignment using the electrode made of the second conductive film as a mask;

forming an electrode made of the first conductive film by etching the first conductive film by self-alignment using the electrode made of the second conductive film as a mask after forming the electrode made of the second conductive film;

forming a second gate electrode by narrowing a line width of the electrode made of the second conductive film by etching;

adding an ~~n-type~~ impurity element to the semiconductor film by self-alignment using the second gate electrode; and

forming a first gate electrode by narrowing a line width of the electrode made of the first conductive film by etching.

4. (Currently amended) A method of fabricating an electrical appliance having a light emitting device, comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

forming an electrode made of the second conductive film by etching the second conductive film;

adding an n-type impurity element to the semiconductor film by using the electrode made of the second conductive film as a mask and by making the n-type impurity element pass through the first conductive film;

forming an electrode made of the first conductive film by etching the first conductive film by self-alignment using the electrode made of the second conductive film as a mask;

forming a second gate electrode by narrowing a line width of the electrode made of the second conductive film by etching;

adding an n-type impurity element to the semiconductor film by using the second gate electrode as a mask and by making the n-type impurity element pass through the electrode made of the first conductive film; and

forming a first gate electrode by narrowing a line width of the electrode made of the first conductive film by etching.

5. (Currently amended) A method of fabricating a light emitting device having at least one thin film transistor in a pixel portion, comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

forming an electrode made of the second conductive film by etching the second conductive film;

adding ~~an n-type~~ a p-type impurity element to the semiconductor film by self-alignment using the electrode made of the second conductive film;

forming an electrode made of the first conductive film by etching the first conductive film by self-alignment using the electrode made of the second conductive film as a mask after forming the electrode made of the second conductive film;

forming a second gate electrode by narrowing a line width of the electrode made of the second conductive film by etching;

adding ~~an n-type~~ a p-type impurity element to the semiconductor film by self-alignment using the second gate electrode as a mask; and

forming a first gate electrode by narrowing a line width of the electrode made of the first conductive film by etching.

6. (Currently amended) A method of fabricating a light emitting device ~~having a pixel portion and a driver circuit formed over a same substrate,~~ comprising the steps of:

forming a semiconductor film on an insulator;

forming a gate insulating film covering the semiconductor film;

forming a first conductive film and a second conductive film on the gate insulating film;

~~forming an electrode made of the second conductive film by~~ etching the second conductive film to form a patterned second conductive film;

adding an n-type impurity element to the semiconductor film by self-alignment using ~~the electrode made of the second conductive film~~ the patterned second conductive film as a mask;

~~forming an electrode made of the first conductive film by~~ etching the first conductive film to form a patterned first conductive film by self-alignment using ~~the electrode made of the~~

~~second conductive film~~ the patterned second conductive film as a mask after etching the second conductive film;

forming a second gate electrode by narrowing a line width of ~~the electrode made of the second conductive film~~ the patterned second conductive film by etching;

adding an n-type impurity element to the semiconductor film by self-alignment using the second gate electrode as a mask; and

forming a first gate electrode by narrowing a line width of ~~the electrode made of the first conductive film~~ the patterned first conductive film by etching.

7. (Original) A method of fabricating a light emitting device according to claim 1, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

8. (Original) A method of fabricating a light emitting device according to claim 2, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

9. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 3, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

10. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 4, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

11. (Original) A method of fabricating a light emitting device according to claim 5, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

12. (Original) A method of fabricating a light emitting device according to claim 6, wherein an n-type impurity region (a) is formed at the former adding step, and an n-type impurity region (b) is formed at the latter adding step.

13. (Original) A method of fabricating a light emitting device according to claim 7, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

14. (Original) A method of fabricating a light emitting device according to claim 8, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

15. (Original) A method of fabricating a light emitting device according to claim 9, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

16. (Original) A method of fabricating a light emitting device according to claim 10, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

17. (Original) A method of fabricating a light emitting device according to claim 11, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

18. (Original) A method of fabricating a light emitting device according to claim 12, wherein a part of the n-type impurity region (b) overlaps the first gate electrode through the gate insulating film.

19. (Original) A method of fabricating a light emitting device according to claim 1, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

20. (Original) A method of fabricating a light emitting device according to claim 2, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

21. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 3, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

22. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 4, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

23. (Original) A method of fabricating a light emitting device according to claim 5, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

24. (Original) A method of fabricating a light emitting device according to claim 6, wherein the first conductive film is a tantalum nitride film, and the second conductive film is a tungsten film.

25. (Original) A method of fabricating a light emitting device according to claim 1, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

26. (Original) A method of fabricating a light emitting device according to claim 2, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

27. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 3, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

28. (Original) A method of fabricating an electrical appliance a light emitting device according to claim 4, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

29. (Original) A method of fabricating a light emitting device according to claim 5, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

30. (Original) A method of fabricating a light emitting device according to claim 6, wherein the first conductive film is a tungsten film, and the second conductive film is an aluminum alloy film.

31. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 3, wherein said electrical appliance is an appliance selected from the group consisting of: a video camera, a digital camera, a DVD, a portable computer, a personal computer, a portable telephone and an audio.

32. (Original) A method of fabricating an electrical appliance having a light emitting device according to claim 4, wherein said electrical appliance is an appliance selected from the group consisting of: a video camera, a digital camera, a DVD, a portable computer, a personal computer, a portable telephone and an audio.